

SINGLE 3-INPUT POSITIVE OR-AND GATE

Check for Samples: SN74LVC1G3208-EP

FEATURES

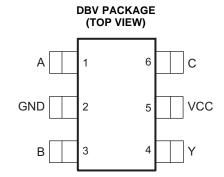
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 5 ns at 3.3 V
- Low Power Consumption, 12.5-µA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Input Hysteresis Allows Slow Input Transition and Better Switching Noise Immunity at the Input

 $(V_{hys} = 250 \text{ mV Typ at } 3.3 \text{ V})$

- Can Be Used in Three Combinations:
 - OR-AND Gate
 - OR Gate
 - AND Gate
- I_{off} Supports Partial-Power-Down Mode Operation

SUPPORTS DEFENSE, AEROSPACE, AND MEDICAL APPLICATIONS

- Controlled Baseline
- One Assembly and Test Site
- One Fabrication Site
- Available in Military (-55°C to 125°C)
 Temperature Ranges (1)
- Extended Product Life Cycle
- Extended Product-Change Notification
- Product Traceability



(1) Custom temperature ranges available

DESCRIPTION/ORDERING INFORMATION

This device is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G3208 is a single 3-input positive OR-AND gate. It performs the Boolean function $Y = (A + B) \cdot C$ in positive logic.

By tying one input to GND or V_{CC} , the SN74LVC1G3208 offers two more functions. When C is tied to V_{CC} , this device performs as a 2-input OR gate (Y = A + B). When A is tied to GND, the device works as a 2-input AND gate (Y = B \cdot C). This device also works as a 2-input AND gate when B is tied to GND (Y = A \cdot C).

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Table 1. ORDERING INFORMATION(1)

T _A	T _A PACKAGE		ORDERABLE PART NUMBER	TOP-SIDE MARKING	VID NUMBER	
–55°C to 125°C	C SOT (SOT-23) – DBV Reel of 250		74LVC1G3208MDBVTEP	CDD5M	V62/13605-01XE	

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

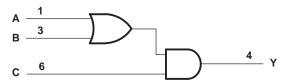


FUNCTION TABLE(1)

	INPUTS					
Α	В	С	Y			
Н	Х	Н	Н			
X	Н	Н	Н			
X	X	L	L			
L	L	Н	L			

(1) X = Valid H or L

LOGIC DIAGRAM (POSITIVE LOGIC)



FUNCTION SELECTION TABLE

LOGIC FUNCTION	FIGURE
2-Input AND Gate	1
2-Input OR Gate	2
$Y = (A + B) \cdot C$	3

LOGIC CONFIGURATIONS

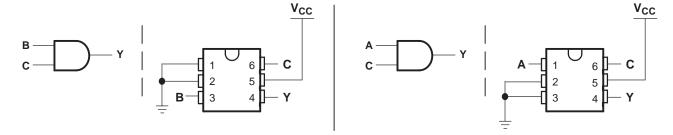


Figure 1. 2-Input AND Gate

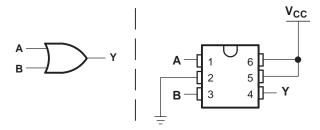


Figure 2. 2-Input OR Gate

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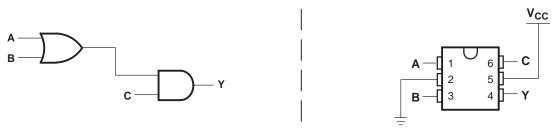


Figure 3. $Y = (A + B) \cdot C$

Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range ⁽²⁾	-0.5	6.5	V	
Vo	Voltage range applied to any output in the high-impe	-0.5	6.5	V	
Vo	Voltage range applied to any output in the high or lo	w state ^{(2) (3)}	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T _{stg}	Storage temperature range	-65	150	°C	

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of VCC is provided in the recommended operating conditions table.

THERMAL INFORMATION

		SN74LVC1G3208	
	THERMAL METRIC ⁽¹⁾	DBV	UNITS
		6 PINS	
θ_{JA}	Junction-to-ambient thermal resistance (2)	207	
θ_{JCtop}	Junction-to-case (top) thermal resistance (3)	148.1	
θ_{JB}	Junction-to-board thermal resistance (4)	50.6	°C // //
ΨЈТ	Junction-to-top characterization parameter (5)	41.2	°C/W
ΨЈВ	Junction-to-board characterization parameter ⁽⁶⁾	50.1	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance (7)	N/A	

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7. in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, ψ_{JT} , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

Product Folder Links: SN74LVC1G3208-EP



Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT	
\ /	Cupply voltage	Operating	1.65	5.5	V	
V_{CC}	Supply voltage	Data retention only	1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}			
V	High-level input voltage	V _{CC} = 2.3 V to 2.7 V	1.7		V	
V_{IH}		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2		V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.7 × V _{CC}			
		V _{CC} = 1.65 V to 1.95 V	(0.35 × V _{CC}		
\ /		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	\/	
V_{IL}	Low-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.8	V	
		V _{CC} = 4.5 V to 5.5 V		1.4		
VI	Input voltage		0	5.5	V	
Vo	Output voltage		0	V_{CC}	V	
		V _{CC} = 1.65 V		-4		
		V _{CC} = 2.3 V		-8		
I _{OH}	High-level output current	V _{CC} = 3 V		-16		
				-24	-	
		V _{CC} = 4.5 V		-32		
		V _{CC} = 1.65 V		4		
		V _{CC} = 2.3 V		8		
l _{OL}	Low-level output current	V _{CC} = 3 V		16	mA	
				24		
		V _{CC} = 4.5 V		32		
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20		
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		ns/V		
	·	V _{CC} = 5 V ± 0.5 V		5		
T _A	Operating free-air temperature		-55	125	°C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

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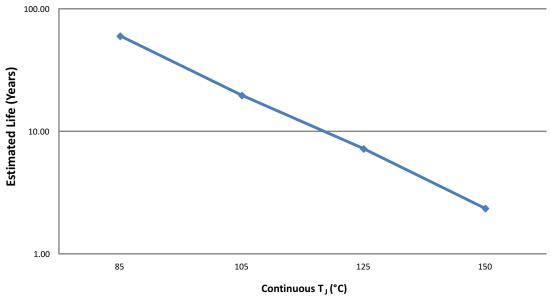


Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMET	TER TEST CONDITIONS	V _{cc}	MIN TYP(1)	MAX	UNIT
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1		
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2		
	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		
V _{OH}	I _{OH} = -16 mA	0.17	2.4		V
	$I_{OH} = -24 \text{ mA}$	3 V	2.3		
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8		
	I _{OL} = 100 μA	1.65 V to 5.5 V		0.11	
	I _{OL} = 4 mA	1.65 V		0.52	
\ /	I _{OL} = 8 mA	2.3 V		0.45	V
V _{OL}	I _{OL} = 16 mA	2.1/		0.68	V
	I _{OL} = 24 mA	3 V		1.1	
	I _{OL} = 32 mA	4.5 V		1.1	
I _I A, B,		0 to 5.5 V	-12.05	8.6	μΑ
I _{off}	V_I or $V_O = 5.5 \text{ V}$	0	-22	41.5	μΑ
I _{CC}	$V_I = 5.5 \text{ V or GND}$ $I_O = 0$	1.65 V to 5.5 V		12.5	μΑ
ΔI _{CC}	One input at $V_{CC} - 0.6 \text{ V}$, Other inputs at V_{CC} or GND	3 V to 5.5 V		500	μΑ
C _i	V _I = V _{CC} or GND	3.3 V	3.5		pF

(1) All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



- (1) See datasheet for absolute maximum and minimum recommended operating conditions.
- (2) Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).
- (3) Enhanced plastic product disclaimer applies.

Figure 4. 74LVC1G3208-EP Operating Life Derating Chart

Product Folder Links: SN74LVC1G3208-EP



Switching Characteristics

only valid for -40°C to 85°C, $C_L = 15 \text{ pF}$ (unless otherwise noted) (see Figure 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)		V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V	
	(INFOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A, B, or C	Υ	3.7	14	2.5	7	1.7	5	1.3	3.4	ns

Switching Characteristics

only valid for -40°C to 85°C, $C_L = 30 pF$ or 50 pF (unless otherwise noted) (see Figure 6)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1 ± 0.15		V _{CC} = 2 ± 0.2		V _{CC} = ± 0.3		V _{CC} = ± 0.5		UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A, B, or C	Y	2.5	17.5	1.8	7.6	1.8	5.9	1.3	4.0	ns

Switching Characteristics

over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 6)

PARAMETER	FROM	TO (OUTPUT)	V _{CC} = 1 ± 0.15		V _{CC} = 2 ± 0.2		V _{CC} = ± 0.3		V _{CC} = ± 0.5		UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A, B, or C	Υ		17.5		7.6		5.9		4.5	ns

Operating Characteristics

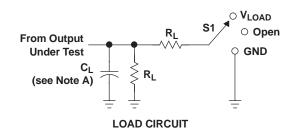
 $T_A = 25^{\circ}C$

	PARAMETER $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	UNIT					
	TAXAMETER	CONDITIONS	TYP	TYP	TYP	TYP	O.u.
C_{pd}	Power dissipation capacitance	f = 10 MHz	15	15	16	17	pF

Product Folder Links: SN74LVC1G3208-EP

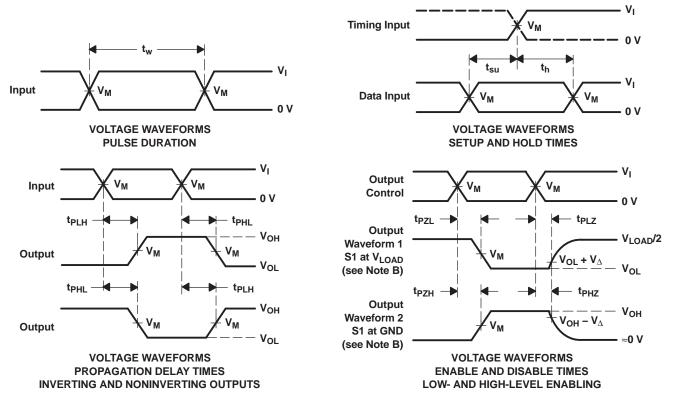


PARAMETER MEASUREMENT INFORMATION



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

.,	INF	PUTS	V _M	· ·			.,
V _{CC}	VI	V _I t _r /t _f		V _{LOAD}	CL	R _L	V_{Δ}
1.8 V \pm 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	15 pF	1 M Ω	0.15 V
2.5 V \pm 0.2 V	V_{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	15 pF	1 M Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 M Ω	0.3 V
5 V \pm 0.5 V	V_{CC}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	15 pF	1 M Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

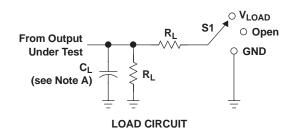
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50~\Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms

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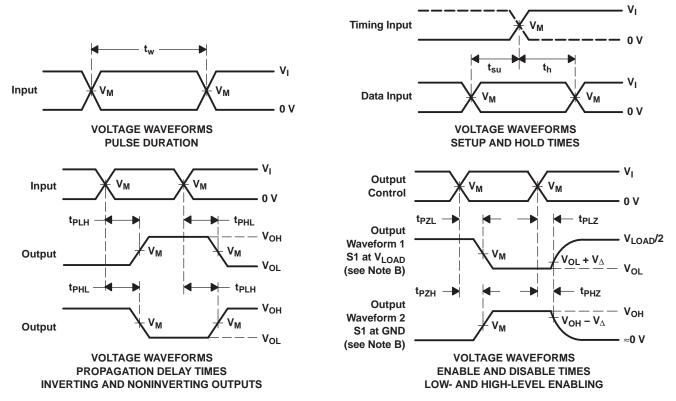


PARAMETER MEASUREMENT INFORMATION



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

.,	INF	PUTS	.,	.,		_	.,
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R _L	V_Δ
1.8 V \pm 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	V _{CC}	≤ 2 ns	V _{CC} /2	2×V _{CC}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	V _{CC}	≤2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \ \Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 6. Load Circuit and Voltage Waveforms

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PACKAGE OPTION ADDENDUM

25-Sep-2019

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74LVC1G3208MDBVTEP	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CDD5M	Samples
V62/13605-01XE	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CDD5M	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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25-Sep-2019

OTHER QUALIFIED VERSIONS OF SN74LVC1G3208-EP:

● Catalog: SN74LVC1G3208

• Automotive: SN74LVC1G3208-Q1

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC1G3208MDBVTEP	SOT-23	DBV	6	250	178.0	9.2	3.3	3.2	1.55	4.0	8.0	Q3

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC1G3208MDBVTEP	SOT-23	DBV	6	250	180.0	180.0	18.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation. 5. Refernce JEDEC MO-178.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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